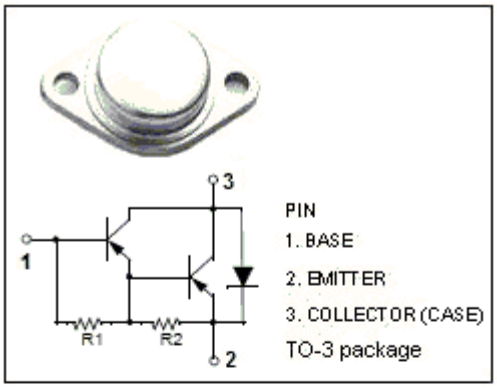
isc Silicon PNP Darlingtion Power Transistor MJ4030

DESCRIPTION

- With TO-3 package
- Respectively complement to type MJ4035
- DARLINGTON
- High DC current gain

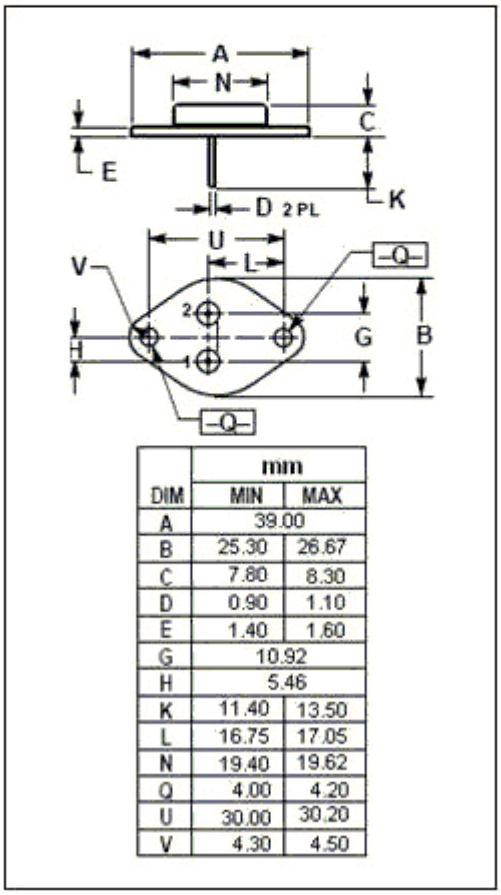


APPLICATIONS

- For use as output devices in complementary general purpose amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_C=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-16	A
I_B	Base Current	-0.5	A
P_C	Collector Power Dissipation@T_C=25℃	150	W
T_J	Junction Temperature	200	℃
T_{stg}	Storage Temperature	-55~200	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.17	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{CEO}	Collector-Emitter Breakdown Voltage	I_C=-100mA; I_B= 0	-60		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C=-10A; I_B=-40mA		-2.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C=-16A; I_B=-80mA		-4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C=-5A; I_B=-400mA		-3	V
$V_{BE(on)}$	Base-Emitter On voltage	I_C=-10A ; V_{CE}=-3V		-3	V
I_{CER}	Collector Cutoff Current	V_{CB}=-60V; R_{BE}= 1KΩ ; V_{CB}=-60V; R_{BE}= 1KΩ ; T_C= 150℃		-1 -5	mA
I_{CEO}	Collector Cutoff current	V_{CE}=-30V; I_B=0		-3	mA
I_{EBO}	Emitter Cut-off current	V_{EB}=-5V; I_C= 0		-5	mA
h_{FE}	DC Current Gain	I_C=-10A ; V_{CE}=-3V	1000		